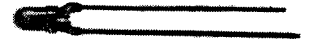
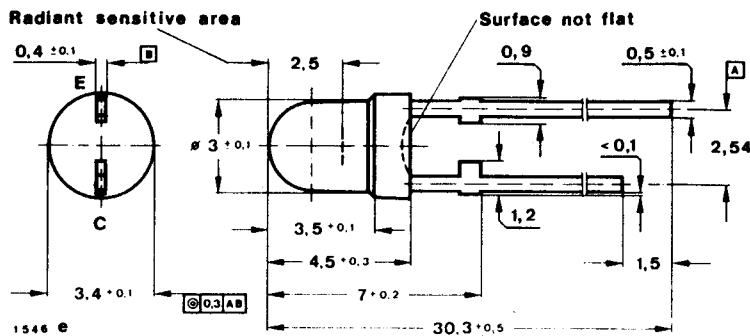


**Silicon NPN Epitaxial Planar Phototransistor**

**Application:** Detector in electronic control and drive circuits

**Features:**

- Plastic case  $\varnothing$  3 mm
- Suitable for visible and near infrared radiation
- High sensitivity
- Wide angle of half sensitivity
- Axial terminals

**Preliminary specifications**
**Dimensions in mm**

 Angle of half sensitivity  $\alpha = 180^\circ$ 

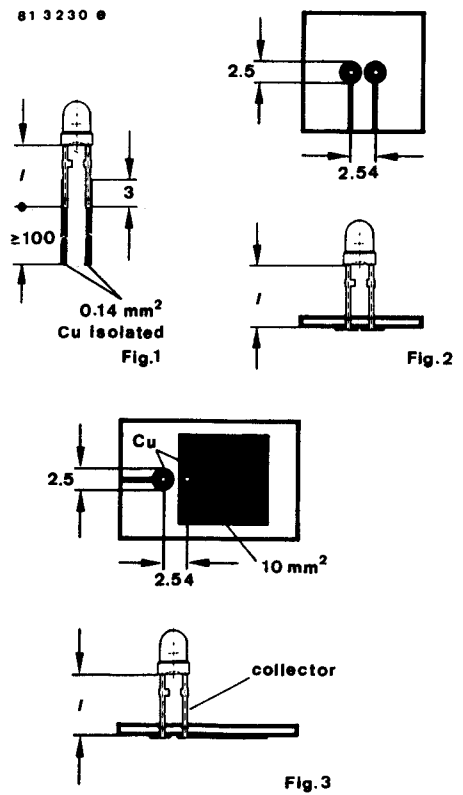
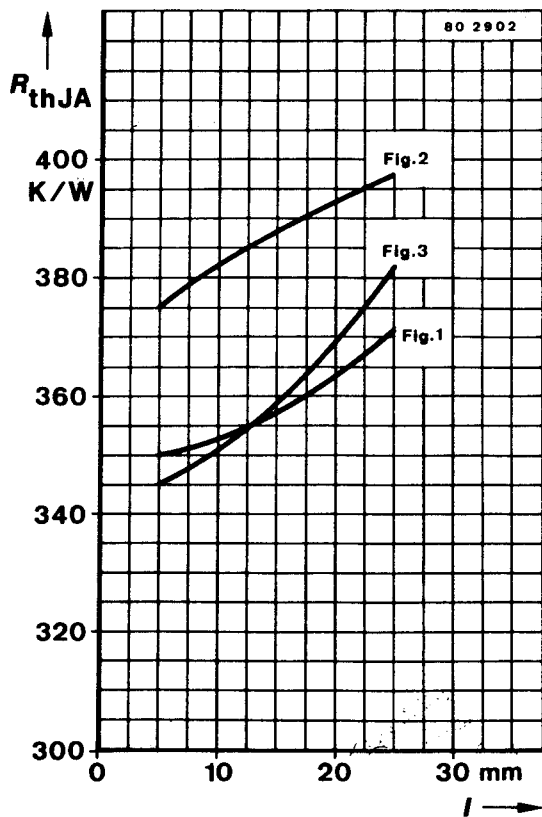
 Special case  
 Clear plastic  
 Weight max. 0.35 g

**Absolute maximum ratings**

Collector-emitter voltage	$V_{CEO}$	32	V
Emitter-collector voltage	$V_{ECO}$	5	V
Collector current	$I_C$	50	mA
Peak collector current			
$\frac{t_p}{T} = 0.5, t_p \leq 10 \text{ ms}$	$I_{CM}$	100	mA
Total power dissipation			
$T_{amb} \leq 55^\circ \text{C}$	$P_{tot}$	100	mW
Junction temperature	$T_j$	100	$^\circ \text{C}$
Storage temperature range	$T_{stg}$	-25 ... +100	$^\circ \text{C}$
Soldering temperature, maximal			
$t \leq 3 \text{ s}$	$T_{sd}^{1)}$	245	$^\circ \text{C}$

 1) Distance from the touching border  $\geq 1.5 \text{ mm}$  with intermediate PC-board

# BPW 42



## Thermal resistance

Junction ambient

$R_{thJA}$

Min. Typ. Max.

450

K/W

## Optical and electrical characteristics

$T_{amb} = 25^\circ C$

Collector dark current

$V_{CE} = 20 V, E = 0$

$I_{CEO}^*)$

10

200

nA

Collector light current

$V_{CE} = 5 V, E_A = 1 \text{ klx}^1)$

$I_{ca}$

3

mA

$V_{CE} = 5 V, E_e = 1 \text{ mW/cm}^2, \lambda_p = 950 \text{ nm}$

$I_{ca}^*)$

0.5

1.0

mA

Peak wavelength sensitivity

$\lambda_p$

830

nm

Range of spectral bandwidth (50 %)

$\lambda_{0.5}$

560 ... 980

nm

Collector-emitter breakdown voltage

$I_C = 1 \text{ mA}$

$V_{(BR)CEO}^*)$

32

V

Collector-emitter saturation voltage

$I_C = 0.1 \text{ mA}, E_e = 1 \text{ mW/cm}^2, \lambda_p = 950 \text{ nm}$

$V_{CEsat}^*)$

0.3

V

\*) AQL = 0.65 %

1) Standard illuminant A (DIN 5033/IEC 306-1)

